



Improved Quad CMOS Analog Switches

DESCRIPTION

The DG201B, DG202B analog switches are highly improved versions of the industry-standard DG201A, DG202. These devices are fabricated in Vishay Siliconix' proprietary silicon gate CMOS process, resulting in lower on-resistance, lower leakage, higher speed, and lower power consumption.

These quad single-pole single-throw switches are designed for a wide variety of applications in telecommunications, instrumentation, process control, computer peripherals, etc. An improved charge injection compensation design minimizes switching transients. The DG201B and DG202B can handle up to ± 22 V input signals, and have an improved continuous current rating of 30 mA. An epitaxial layer prevents latchup.

All devices feature true bi-directional performance in the on condition, and will block signals to the supply voltages in the off condition.

The DG201B is a normally closed switch and the DG202B is a normally open switch. (see Truth Table.)

FEATURES

- ± 22 V supply voltage rating
- TTL and CMOS compatible logic
- Low on-resistance $R_{DS(on)}$: 45 Ω
- Low leakage I_{D(on)}: 20 pA
- Single supply operation possible
- Extended temperature range
- Fast switching t_{ON}: 120 ns
- Low glitching Q: 1 pC
- Compliant to RoHS Directive 2002/95/EC

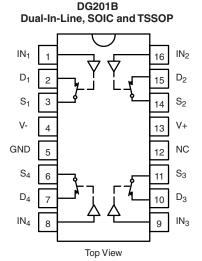
BENEFITS

- Wide analog signal range
- Simple logic interface
- Higher accuracy
- Minimum transients
- Reduced power consumption
- Superior to DG201A, DG202
- Space savings (TSSOP)

APPLICATIONS

- Industrial instrumentation
- Test equipment
- Communications systems
- Disk drives
- Computer peripherals
- Portable instruments
- Sample-and-hold circuits

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE							
Logic DG201B DG202B							
0	ON	OFF					
1	OFF	ON					

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

Document Number: 70037 S11-0800-Rev. J, 25-Apr-11

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply



ORDERING INFORMATION					
Temp. Range	Package	Part Number			
- 55 °C to 125 °C	16-pin CerDIP	DG201BAK			
- 55 C to 125 C	то-ріп Сегдіғ	DG202BAK			
	16 nin Plantia DID	DG201BDJ DG201BDJ-E3			
	16-pin Plastic DIP	DG202BDJ DG202BDJ-E3			
	16 pie powow COIC	DG201BDY DG201BDY-E3 DG201BDY-T1 DG201BDY-T1-E3			
- 40 °C to 85 °C	16-pin narrow SOIC	DG202BDY DG202BDY-E3 DG202BDY-T1 DG202BDY-T1-E3			
	16 pin TSSOR	DG201BDQ DG201BDQ-E3 DG201BDQ-T1 DG201BDQ-T1-E3			
	16-pin TSSOP	DG202BDQ DG202BDQ-E3 DG202BDQ-T1 DG202BDQ-T1-E3			

ABSOLUTE MAXIMUM RATINGS					
Parameter		Limit	Unit		
Voltages Referenced, V+ to V-		44			
GND		25	V		
Digital Inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first	v		
Current (Any terminal)		30	m ^		
Peak Current S or D (Pulsed at 1 ms, 10 % duty cycle max.)		100	mA		
Storage Temperature	(AK, DK suffix)	- 65 to 150	°C		
Storage Temperature	(DJ, DY, DQ suffix)	- 65 to 125]		
16-pin plastic DIP ^c		470			
Power Dissipation (Package) ^b	16-pin narrow SOIC and TSSOP ^d	640	\/		
rower Dissipation (Package)	16-pin CerDIP ^e	900	mW		
	LCC-20 ^f	750			

Notes:

- a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 6.5 mW/°C above 75 °C.
- d. Derate 7.6 mW/°C above 75 °C.
- e. Derate 12 mW/°C above 75 °C.
- f. Derate 10 mW/°C above 75 °C.



SCHEMATIC DIAGRAM (typical channel)

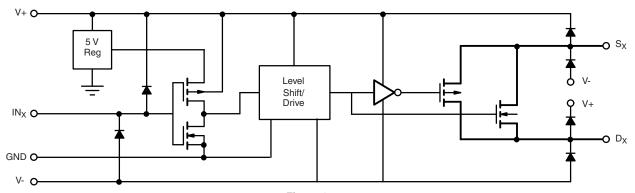


Figure 1.

SPECIFICATIONS ^a									
		Test Conditions			A Suffix		D Suffix - 40 °C to 85 °C		
		Unless Specified V+ = 15 V, V- = - 15 V			- 55 °C t	o 125 °C	- 40 °C	to 85 °C	
Parameter	Symbol	$V_{1N} = 13 \text{ V}, V_{1N} = -13 \text{ V}$ $V_{1N} = 2.4 \text{ V}, 0.8 \text{ V}^{\text{f}}$	Temp.b	Typ.c	Min. ^d	Max.d	Min. ^d	Max. ^d	Unit
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		- 15	15	- 15	15	V
Drain-Source On-Resistance	R _{DS(on)}	V _D = ± 10 V, I _S = 1 mA	Room Full	45		85 100		85 100	Ω
R _{DS(on)} Match	$\Delta R_{DS(on}$	<i>b</i>	Room	2					
Source Off Leakage Current	I _{S(off)}	$V_S = \pm 14 \text{ V}, V_D = \pm 14 \text{ V}$	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	
Drain Off Leakage Current	I _{D(off)}	$V_D = \pm 14 \text{ V}, V_S = \pm 14 \text{ V}$	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	nA
Drain On Leakage Current	I _{D(on)}	$V_S = V_D = \pm 14 \text{ V}$	Room Full	± 0.02	- 0.5 - 40	0.5 40	- 0.5 - 10	0.5 10	
Digital Control									
Input Voltage High	V_{INH}		Full		2.4		2.4		V
Input Voltage Low	V_{INL}		Full			0.8		0.8	, v
Input Current	I _{INH} or I _{INL}	V _{INH} or V _{INL}	Full		- 1	1	- 1	1	μΑ
Input Capacitance	C _{IN}		Room	5					pF
Dynamic Characteristics	3								
Turn-On Time	t _{ON}	V _S = 2 V	Room Full	120		300		300	ns
Turn-Off Time	t _{OFF}	see switching time test circuit	Room Full	65		200		200	115
Charge Injection	Q	$C_L = 1000 \text{ pF, } V_g = 0 \text{ V}$ $R_g = 0 \Omega$	Room	1					рС
Source-Off Capacitance	C _{S(off)}	$V_S = 0 \text{ V, f} = 1 \text{ MHz}$	Room	5					
Drain-Off Capacitance	$C_{D(off)}$	•	Room	5					pF
Channel On Capacitance	C _{D(on)}	$V_D = V_S = 0 V$, $f = 1 MHz$	Room	16					
Off Isolation	OIRR	$C_1 = 15 \text{ pF, } R_1 = 50 \Omega$	Room	90					
Channel-to-Channel Crosstalk	X _{TALK}	$V_S = 1 V_{RMS}, f = 100 \text{ kHz}$	Room	95					dB
Power Supply									
Positive Supply Current	l+	V _{IN} = 0 or 5 V	Room Full			50 100		50 100	μΑ
Negative Supply Current	l-	v IV – 0 01 0 v	Room Full		- 1 - 5		- 1 - 5		μл
Power Supply Range for Continuous Operation	V _{OP}		Full		± 4.5	± 22	± 4.5	± 22	٧



SPECIFICATIONS (for Single Supply) ^a									
		Test Conditions Unless Specified				uffix o 125 °C	_	uffix to 85 °C	
Parameter	Symbol	V+ = 12 V, V- = 0 V $V_{IN} = 2.4 V, 0.8 V^f$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		0	12	0	12	V
Drain-Source On-Resistance	R _{DS(on)}	V _D = 3 V, 8 V, I _S = 1 mA	Room Full	90		160 200		160 200	Ω
Dynamic Characteristics	3						•		
Turn-On Time	t _{ON}	V _S = 8 V	Room	120		300		300	no
Turn-Off Time	t _{OFF}	see switching time test circuit	Room	60		200		200	ns
Charge Injection	Q	$C_L = 1 \text{ nF, V}_{gen} = 6 \text{ V}$ $R_{gen} = 0 \Omega$	Room	4					рС
Power Supply	Power Supply								
Positive Supply Current	l+	V _{IN} = 0 or 5 V	Room Full			50 100		50 100	μА
Negative Supply Current	I-	VIV = 0 01 9 V	Room Full		- 1 - 5		- 1 - 5		μΑ
Power Supply Range for Continuous Operation	V _{OP}		Full		+ 4.5	+ 25	+ 4.5	+ 25	٧

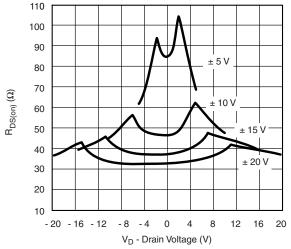
Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 °C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

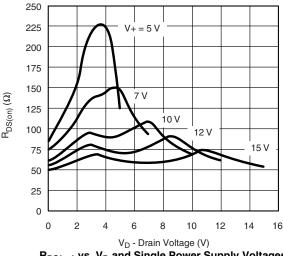
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



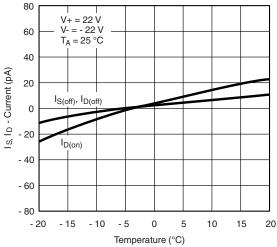
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



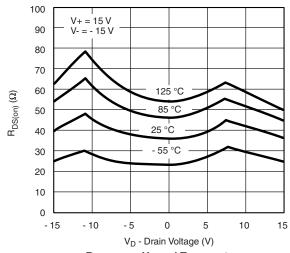
R_{DS(on)} vs. V_D and Power Supply Voltages



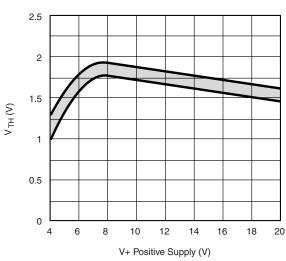
 $R_{DS(on)}$ vs. V_D and Single Power Supply Voltages



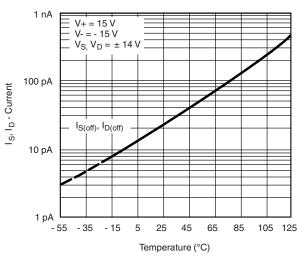
Leakage Currents vs. Analog Voltage



 $R_{DS(on)}\, vs. \; V_D$ and Temperature

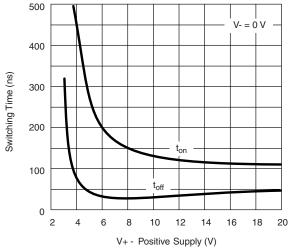


Input Switching Threshold vs. Supply Voltage

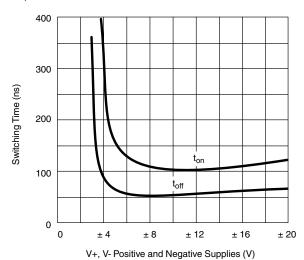


Leakage Currents vs. Temperature

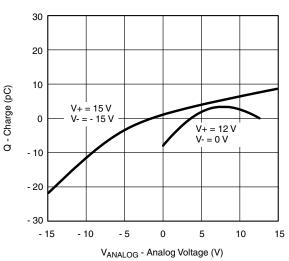
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



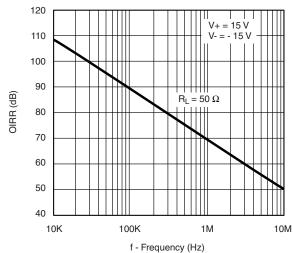
Switching Time vs. Single Supply Voltage



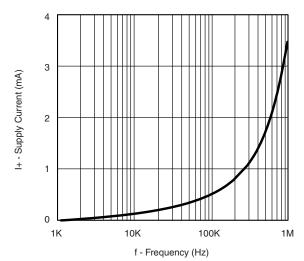
Switching Time vs. Power Supply Voltage



Q_S, Q_D - Charge Injection vs. Analog Voltage



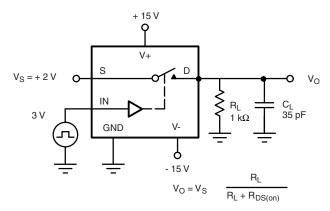
Off Isolation vs. Frequency



Supply Current vs. Switching Frequency



TEST CIRCUITS



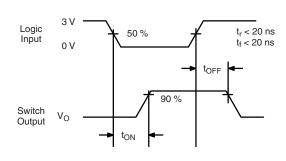


Figure 2. Switching Time

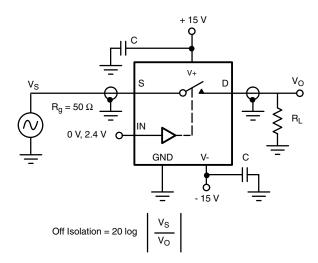


Figure 3. Off Isolation

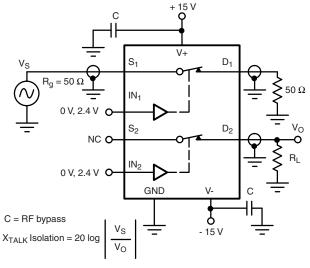
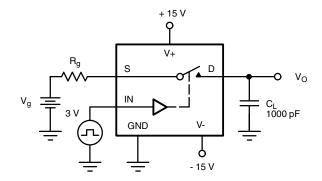
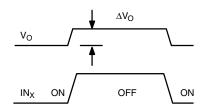


Figure 4. Channel-to-Channel Crosstalk





 ΔV_O = measured voltage error due to charge injection The charge injection in coulombs is Q = C_L x ΔV_O

Figure 5. Charge Injection

APPLICATIONS

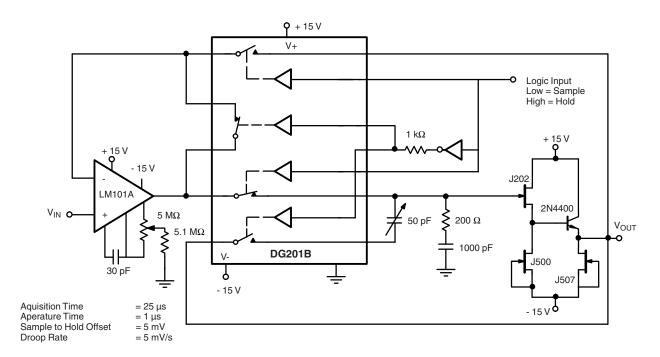


Figure 6. Sample-and-Hold

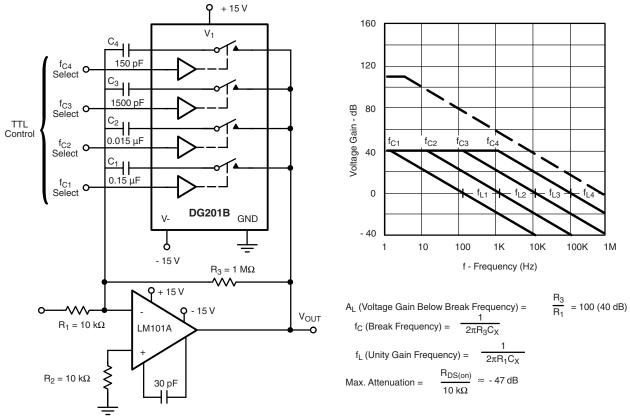


Figure 7. Active Low Pass Filter with Digitally Selected Break Frequency



APPLICATIONS

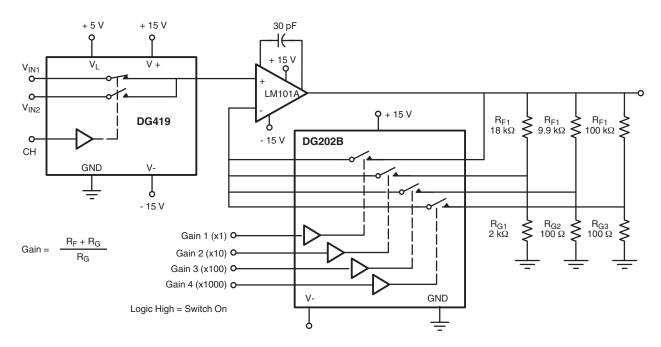
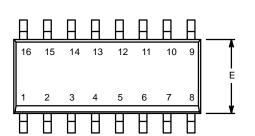


Figure 8. A Precision Amplifier with Digitally Programable Input and Gains

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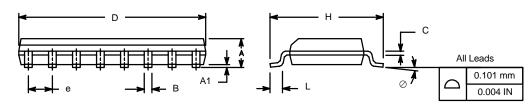
SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012



	MILLIMETERS		INC	HES		
Dim	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.38	0.51	0.015	0.020		
С	0.18	0.23	0.007	0.009		
D	9.80	10.00	0.385	0.393		
E	3.80	4.00	0.149	0.157		
е	1.27	BSC	0.050	BSC		
Н	5.80	6.20	0.228	0.244		
L	0.50	0.93	0.020	0.037		
0	0°	8°	0°	8°		
ECN: S-03946—Rev. E.09- Jul-01						

ECN: S-03946—Rev. F, 09-Jul-01

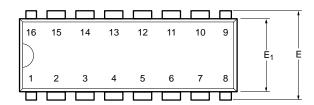
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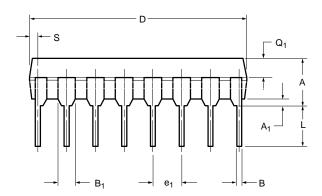


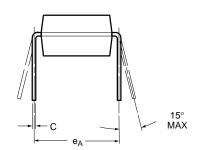
Document Number: 71194 www.vishay.com 02-Jul-01 sww.vishay.com



PDIP: 16-LEAD





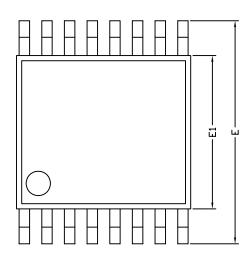


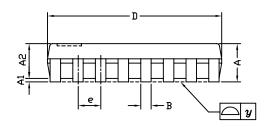
	MILLIMETERS		INC	HES	
Dim	Min	Max	Min	Max	
Α	3.81	5.08	0.150	0.200	
A ₁	0.38	1.27	0.015	0.050	
В	0.38	0.51	0.015	0.020	
B ₁	0.89	1.65	0.035	0.065	
С	0.20	0.30	0.008	0.012	
D	18.93	21.33	0.745	0.840	
E	7.62	8.26	0.300	0.325	
E ₁	5.59	7.11	0.220	0.280	
e ₁	2.29	2.79	0.090	0.110	
e _A	7.37	7.87	0.290	0.310	
L	2.79	3.81	0.110	0.150	
Q_1	1.27	2.03	0.050	0.080	
S	0.38	1.52	.015	0.060	
ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482					

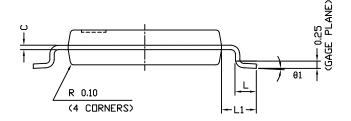
Document Number: 71261 www.vishay.com 06-Jul-01 www.vishay.com



TSSOP: 16-LEAD







	DII	MENSIONS IN MILLIMETER	S
Symbols	Min	Nom	Max
Α	-	1.10	1.20
A1	0.05	0.10	0.15
A2	=	1.00	1.05
В	0.22	0.28	0.38
С	=	0.127	=
D	4.90	5.00	5.10
E	6.10	6.40	6.70
E1	4.30	4.40	4.50
е	-	0.65	-
L	0.50	0.60	0.70
L1	0.90	1.00	1.10
у	=	-	0.10
θ1	0°	3°	6°
ECN: S-61920-Rev. D, 23-0	Oct-06		

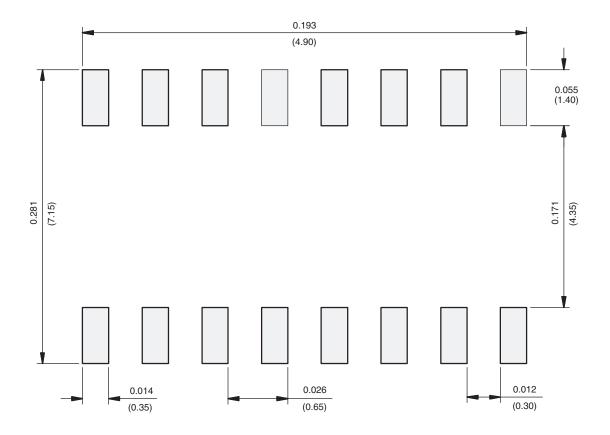
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DWG: 5624

Document Number: 74417
23-Oct-06
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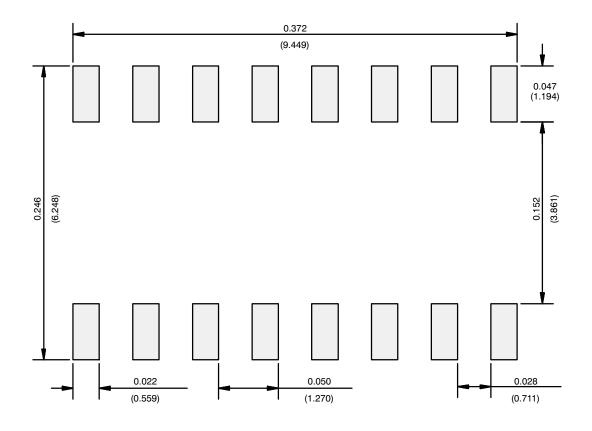
RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads Dimensions in inches (mm)



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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